# MSD42WT1G, NSVMSD42WT1G

# NPN High Voltage Transistors

This NPN Silicon Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

## **Features**

- These Devices are Pb-Free, Halogen Free and are RoHS Compliant
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

# **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	300	V
Collector-Emitter Voltage	V <sub>(BR)CEO</sub>	300	V
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	6.0	V
Collector Current - Continuous	Ic	150	mA

### THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P <sub>D</sub>	450	mW
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	274	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## **ELECTRICAL CHARACTERISTICS**

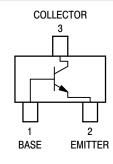
Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage $(I_C = 1.0 \text{ mA}, I_B = 0)$	V <sub>(BR)CEO</sub>	300	-	V
Collector-Base Breakdown Voltage ( $I_C = 100 \mu A, I_E = 0$ )	V <sub>(BR)CBO</sub>	300	ı	>
Emitter-Base Breakdown Voltage ( $I_E = 100 \mu A, I_E = 0$ )	V <sub>(BR)EBO</sub>	6.0	-	٧
Collector-Base Cutoff Current (V <sub>CB</sub> = 200 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	0.1	μΑ
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_B = 0)$	I <sub>EBO</sub>	-	0.1	μΑ
DC Current Gain (Note 2) (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1.0 mA) (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 30 mA)	h <sub>FE1</sub>	25 40	- -	-
Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 20 mA, I <sub>B</sub> = 2.0 mA)	V <sub>CE(sat)</sub>	-	0.5	V

- 1. FR-4 @ 10 mm<sup>2</sup>, 1 oz. Copper traces.
- 2. Pulse Test: Pulse Width  $\leq$  300 µs, D.C.  $\leq$  2%.



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SC-70 (SOT-323) CASE 419 STYLE 3

### **MARKING DIAGRAM**



1D = Specific Device Code

M = Date Code

= Pb-Free Package

# ORDERING INFORMATION

(Note: Microdot may be in either location)

Device	Package	Shipping <sup>†</sup>
MSD42WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
NSVMSD42WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## TYPICAL CHARACTERISTICS

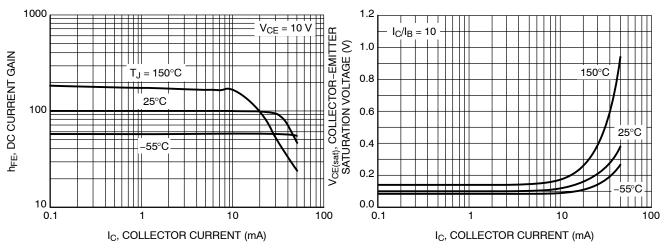


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

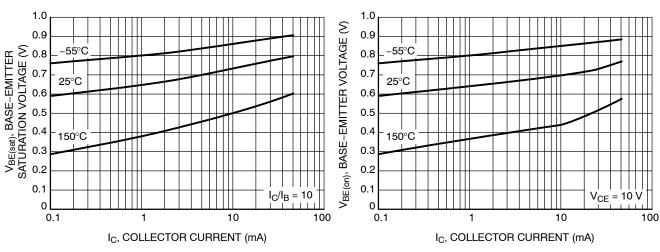


Figure 3. Base-Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base–Emitter On Voltage vs.
Collector Current

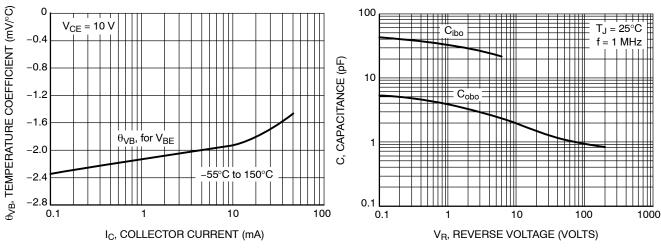
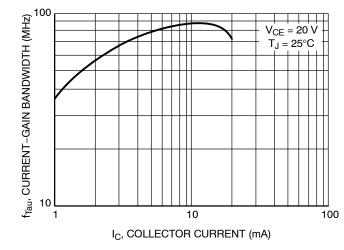


Figure 5. Base–Emitter Temperature Coefficient

Figure 6. Capacitance

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# TYPICAL CHARACTERISTICS



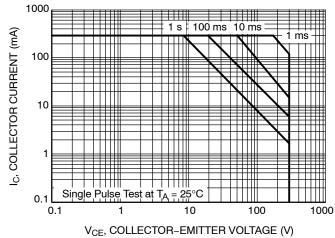
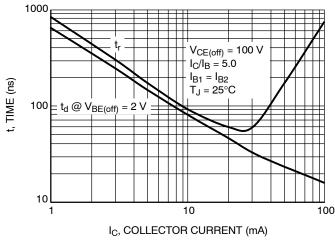


Figure 7. Current-Gain — Bandwidth Product

Figure 8. Safe Operating Area



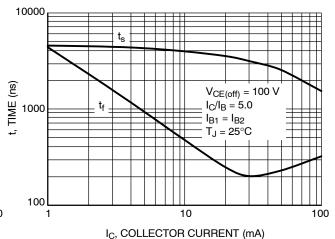


Figure 9. Turn-On Time

Figure 10. Turn-Off Time





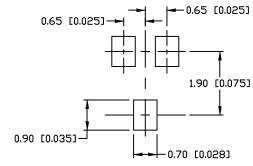
SC-70 (SOT-323) CASE 419 ISSUE P

**DATE 07 OCT 2021** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF		0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095
E e e1 L	1.15 1.20 0.20	1.24 1.30 0.65 BS0 0.38	1.35 1.40 0.56	0.045 0.047 0.008	0.049 0.051 0.026 BS 0.015	0.0 0.0 C



For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

# TOP VIEW SIDE VIEW END VIEW

# GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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